



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Tikashi AKATSU *et al.*

Confirmation No.: 2653

Application No: 10/663,917

Group Art Unit: 2811

Filing Date: September 17, 2003

Examiner: Not Assigned

For: WAFER WITH A RELAXED USEFUL
LAYER AND METHOD OF FORMING THE
WAFER

Attorney Docket No.: 4717-8900

SECOND INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Arlinghambria, Virginia 22313-1450

Sir:

Pursuant to Applicant's duty of disclosure under 37 C.F.R. § 1.56, enclosed is a Form PTO-1449 which lists fifteen (15) references for the Examiner's review. Also enclosed is a copy of the French and International Search Reports from the corresponding foreign applications on which the references were cited.

Copies of non-U.S. patent references B1-B2 and C1-C2 are enclosed herewith. Copies of U.S. patent references A1-A11 will be provided if the Examiner so requests.

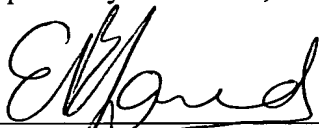
It is respectfully requested that the references be made of record in this application by the Examiner's completion and return of the attached Form PTO-1449.

This Second Information Disclosure Statement is being submitted under 37 C.F.R. §1.97(b)(3), prior to the mailing of a first Office Action on the merits; thus no fee is believed to be required. Should any fees be required, however, please charge such fees to Winston & Strawn LLP Deposit Account No. 50-1814.

Respectfully submitted,

April 27, 2004

Date



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WINSTON & STRAWN LLP
Customer No. 28765

202-371-5771

LIST OF REFERENCES CITED BY APPLICANT Form PTO-1449 <i>(Use several sheets if necessary)</i>					ATTY. DOCKET NO.: 4717-8900		APPLICATION NO.: 10/663,917	
Sheet 1 of 1					APPLICANT: Tukeshi AKATSU et al.		GROUP: 2811	
					FILING DATE: September 17, 2003			

O I P E
 APR 27 2004
 PATENT & TRADEMARK OFFICE

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	CITE NO.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A1	6,100,166	08/2000	Sakaguchi et al.	438	455	
	A2	2002/0125497 A1	09/2002	Fitzgerald	257	191	
	A3	2002/0123183 A1	09/2002	Fitzgerald	438	199	
	A4	6,521,041 B2	02/2003	Wu et al.	117	94	
	A5	6,534,382 B1	03/2003	Sakaguchi et al.	438	455	
	A6	2003/0077867	04/2003	Fitzgerald	438	285	
	A7	6,593,641 B1	07/2003	Fitzgerald	257	616	
	A8	2003/0203547 A1	10/2003	Sakaguchi et al.	438	151	
	A9	6,646,322 B2	11/2003	Fitzgerald	257	531	
	A10	2004/0000268 A1	01/2004	Wu et al.	11	94	
	A11	6,677,192 B1	01/2004	Fitzgerald	438	172	

FOREIGN PATENT DOCUMENTS								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	B1	WO 99/53539 A	10/1999	WIPO				
	B2	WO 02/071495 A	12/2002	WIPO				

OTHER REFERENCES <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>	
C1	Cheng, Z-Y et al., "SiGe-On-Insulator (SGOI): Substrate Preparation and MOSFET Fabrication for Electron Mobility Evaluation," IEEE International SOI Conference, pp. 13-14, October 2001
C2	Tong, Q.Y. et al., "Semiconductor Wafer Bonding" (extracts), Science and Technology, Interscience Technology, November 1998

EXAMINER	DATE CONSIDERED
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with **MPEP 609**. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.